ON Semiconductor

Is Now

Onsemi

To learn more about onsemi[™], please visit our website at <u>www.onsemi.com</u>

onsemi and ONSEMI: and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product factures, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application is the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application, Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application, Buyer shall indemnify and hold ons

NGTD8R65F2

Fast Switching Rectifier Die

Fast switching low Vf rectifier die for free-wheeling applications.

Features

- Fast Switching
- Low Vf

Typical Applications

- Industrial Motor Control
- Solar PV Inverters

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RRM}	650	V
Max Forward Conduction Current	۱ _F	(Note 1)	А
Maximum Junction Temperature	ТJ	175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on thermal properties of assembly.

MECHANICAL DATA

Parameter	Value	Unit	
Die Size	2817 x 2817	μm ²	
Die Thickness	10	mils	
Wafer Size	150	mm	
Top Pad Size (Anode)	2376 x 2376	μm ²	
Top Metal (Anode)	4 μm AISi		
Back Metal (Cathode)	2 μm TiNiAg		
Max possible chips per wafer	1623		
Passivation frontside	Oxide-Nitride		
Reject ink dot size	25 mils		
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Bare Wafer in Jar Storage time: < 36 months	Type: Die on tape in ring-pack Storage time: < 3 months	

ORDERING INFORMATION

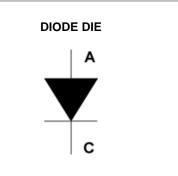
Device	Inking?	Shipping		
NGTD8R65F2WP	Yes	Bare Wafer in Jar		
NGTD8R65F2SWK	Yes	Sawn Wafer on Tape		



ON Semiconductor®

www.onsemi.com

 $V_{RRM} = 650 V$ I_F = Limited by T_{J(max)}



2817 μm CC14 E 92 R = 180 μm 2376 μm

DIE OUTLINE

© Semiconductor Components Industries, LLC, 2016 March, 2016 – Rev. 0

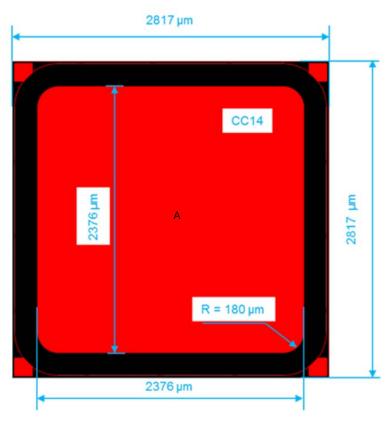
NGTD8R65F2

ELECTRICAL CHARACTERISTICS (T_J = 25° C, unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Units	
STATIC CHARACTERISTICS							
Forward Voltage	I _F = 30 A, T _J = 25°C	V _F		2.1	2.8	V	
Reverse Voltage	I _R = 320 μA, T _J = 25°C	V _R	650			V	
Reverse Current	V_R = 650 V, T_J = 25°C	I _R	-1.0		1.0	μΑ	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



A = Anode pad All dimensions in μm

NGTD8R65F2

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

ON Semiconductor and the intervent and the inter

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative